



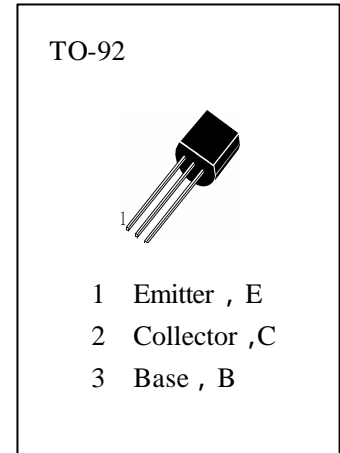
H3203

APPLICATIONS

HIGH CURRENT APPLICATIONS.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation.....	625mW
V_{CBO}	Collector-Base Voltage.....	35V
V_{CEO}	Collector-Emitter Voltage.....	30V
V_{EBO}	Emitter-Base Voltage.....	5V
I_C	Collector Current.....	800mA



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	35			V	$I_C=100\mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	30			V	$I_C=10mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	5			V	$I_E=1mA, I_C=0$
HFE (1)	DC Current Gain	100		320		$V_{CE}=1V, I_C=100mA$
HFE (2)	DC Current Gain	35				$V_{CE}=1V, I_C=700mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.5	V	$I_C=500mA, I_B=20mA$
V_{BE}	Base-Emitter Voltage	0.5		0.8	V	$V_{CE}=1V, I_C=10mA$
I_{CBO}	Collector Cut-off Current			100	nA	$V_{CB}=35V, I_E=0$
I_{EBO}	Emitter Cut-off Current			100	nA	$V_{EB}=5V, I_C=0$
f_T	Current Gain-Bandwidth Product		120		MHz	$V_{CE}=5V, I_C=10mA$
C_{ob}	Output Capacitance		13		pF	$V_{CB}=10V, I_E=0, f=1MHz$

HFE Classification

O

Y

100—200

160—320